(08 Marks)

Eighth Semester B.E. Degree Examination, Aug./Sept.2020 **Nanoelectronics**

Max. Marks: 80 Time: 3 hrs.

Not	e: i) ii)	For Regular Students: Answer any FIVE full questions irrespective of module For Arrear Students: Answer any FIVE full questions, choosing ONE full questions from each module.	estion
		Module-1	
1	a.	Explain quantum electronics. Write a note on upcoming electron devices.	(08 Marks)
	b.	With neat sketch explain about quantum cellular automata.	(08 Marks)
2	0	Write a note on transistor and nanoeffects in FET, SET and BJT.	(08 Marks)
2	a. b.	Discuss about FET versus SET with neat sketch.	(08 Marks)
		Module-2	
3	a.	Enumerate the applications of CNT's.	(08 Marks)
	b.	Describe the three structures of CNT's with neat sketch.	(08 Marks)
		意义来到1954年的1957年的1954年(1964年)。 1967年(1964年)	
4.	a.	Describe organic FET with neat sketch.	(08 Marks)
	b.	Explain FinFET with neat sketch.	(08 Marks)
		Module-3	
5	a.	List out the applications and importance of Nanotubes in FET's.	(08 Marks)
	b.	Describe about the DWNT's. Mention properties and applications.	(08 Marks)
6	a.	With the neat sketch, explain SWNT's. Mention properties and applications.	(08 Marks)
O	b.	Explain the IV characteristics of P-CNTFET and N-CNTFET in detail.	(08 Marks)
		· Module-4	
7	a.	Explain RTD with a neat sketch.	(10 Marks)
	b.	Give a short note on Tunnelling diode. Mention applications.	(06 Marks)
8	a.	Write a note on digital circuit based on RTBT with neat sketch.	(08 Marks
	b.	With neat sketch describe three terminal tunneling diode.	(08 Marks)
		Module-5	
9	a.	Explain tunneling through potential barrier.	(08 Marks
	b.	Discuss about hot electron effect in MOSFET's.	(08 Marks
10	a.	Explain about blockade in quantum dot circuits.	(08 Marks)
10		Discrete design and the state of tunneling Mention applications of tunneling	(08 Marks

b. Briefly explain about Tunneling Junctions. Mention applications of tunneling.